



### PRECISION DUAL MICROPOWER CMOS OPERATIONAL AMPLIFIER

### **GENERAL DESCRIPTION**

The ALD2731A/ALD2731 is a precision dual low-cost high-slew-rate monolithic CMOS micropower operational amplifier intended for a broad range of analog applications using ±1V to ±5V dual power supply systems, as well as +2V to +10V battery operated systems. All device characteristics are specified for +5V single supply or ±2.5V dual supply systems. Supply current is 250µA per amplifier maximum at 5V supply voltage. It is manufactured with Advanced Linear Devices' enhanced EPAD® silicon gate CMOS process.

The ALD2731A/ALD2731 features extremely low input power requirements, practically removing any leading effects on high source impedance signal sources such as cpacitive sensors. These devices do not add any significant errors, regardless of what the souce impedance variations may be, thereby improving overall system precision and accuracy. The device is designed to offer the benefits of CMOS technology by providing a wide range of desired specifications. The most important of these specifications is extremely low input bias/offset currents at extremely low input offset voltages. It has been developed specifically for the +5V single supply or ±1V to ±5V dual supply user and offers the popular industry standard pin configuration of µA741 and ICL7611 types.

Several additional important characteristics of the device make application easier to implement at those voltages. First, the operational amplifier can operate with rail to rail input and output voltages. This means the signal input voltage and output voltage can be equal to the positive and negative supply voltages. This feature allows numerous analog serial stages and flexibility in input signal bias levels. Second, the device was designed to accommodate mixed applications where digital and analog circuits may operate off the same power supply or battery. Third, the output stage can typically drive up to 50pF capacitive and  $10K\Omega$  resistive loads.

These features, combined with extremely low input currents, high open loop voltage gain of 100V/mV, useful bandwidth of 700KHz, a slew rate of 0.7V/us, low power dissipation of 0.5mW, low offset voltage and temperature drift, make the ALD2731A/ALD2731 a versatile, micropower operational amplifier.

The ALD2731A/ALD2731, designed and fabricated with silicon gate CMOS technology, offers 0.01pA typical input bias current. On chip offset voltage trimming, using EPAD technology, allows the device to be used without nulling. Additionally, robust design and rigorous screening make this device especially suitable for operation in temperature-extreme environments and rugged conditions.

### ORDERING INFORMATION ("L" suffix denotes lead-free (RoHS))

Opera	Operating Temperature Range								
0°C to +70°C	0°C to +70°C	-55°C to 125°C							
8-Pin Small Outline Package (SOIC)	8-Pin Plastic Dip Package	8-Pin CERDIP Package							
ALD2731ASAL ALD2731SAL ALD2731ASA ALD2731SA	ALD2731APAL ALD2731PAL ALD2731APA ALD2731PA	ALD2731ADA ALD2731DA							

<sup>\*</sup> Contact factory for leaded (non-RoHS) or high temperature versions.

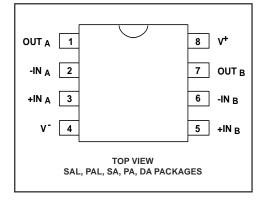
### **FEATURES & BENEFITS**

- Two package versions -- lead-free (RoHS compliant) and legacy leaded (tin-lead)
- Extremely low input offset voltages --0.6mV typical
- Extremely low input bias currents --0.01pA typical
- All parameters specified for +5V single supply or ±2.5V dual supply systems
- Rail to rail input and output voltage ranges
- No frequency compensation required -unity gain stable
- Ideal for high source impedance applications
- Dual power supplies ±1.0V to ±5.0V
- Single power supply +2.0V to +10.0V
- High voltage gain -- typ. 100V/mV @  $\pm 2.5$ V Drive as low as 10K $\Omega$  load
- Output short circuit protected
- Unity gain bandwidth of 0.7MHz
- Slew rate of 0.7V/µs
- Micropower symmetrical complementary output drive
- Suitable for rugged, temperature-extreme environments

### **APPLICATIONS**

- · Voltage amplifier
- Voltage follower/buffer
- Charge integrator
- Photodiode amplifier
- Data acquisition systems
- High performance portable instruments
- Signal conditioning circuits
- Sensor and transducer amplifiers
- Low leakage amplifiers
- Active filters
- Sample/Hold amplifier
- Picoammeter
- Current to voltage converter

### PIN CONFIGURATION



### **ABSOLUTE MAXIMUM RATINGS**

Supply voltage, V+	10.6V
Differential input voltage range	-0.3V to V++0.3V
Power dissipation	600mW
Operating temperature range SAL, PAL, SA, PA packages	0°C to +70°C
DA package	55°C to +125°C
Storage temperature range	65°C to +150°C
Lead temperature, 10 seconds	+260°C

CAUTION: ESD Sensitive Device. Use static control procedures in ESD controlled environment.

# OPERATING ELECTRICAL CHARACTERISTICS $T_A = 25^{\circ}\text{C V}_S = \pm 2.5\text{V}$ unless otherwise specified

		ALD2731A			ALD2731			Test	
Parameter	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Conditions
Supply Voltage	Vs V+	±1.0 2.0		±5.0 10.0	±1.0 2.0		±5.0 10.0	V V	Dual Supply Single Supply
Input Offset Voltage	Vos		0.6	1.0		1.0	2.0	mV	Rs ≤ 100KΩ
Input Offset Current	IOS		0.01	10 200		0.01	10 200	pA pA	T <sub>A</sub> = 25°C 0°C ≤ T <sub>A</sub> ≤ +70°C
Input Bias Current	IB		0.01	10 200		0.01	10 200	pA pA	T <sub>A</sub> = 25°C 0°C ≤ T <sub>A</sub> ≤ +70°C
Input Voltage Range	VIR	-0.3 -2.8		+5.3 +2.8	-0.3 -2.8		+5.3 +2.8	V V	V+ = +5V VS = ±2.5V
Input Resistance	RIN		10 <sup>14</sup>			10 <sup>14</sup>		Ω	
Input Offset Voltage Drift	TCVos		5			5		μV/°C	RS ≤ 100KΩ
Power Supply Rejection Ratio	PSRR		85 85			85 85		dB dB	RS ≤ 100KΩ 0°C ≤ TA ≤ +70°C
Common Mode Rejection Ratio	CMRR		85 85			85 85		dB dB	RS ≤ 100KΩ 0°C ≤ TA ≤ +70°C
Large Signal Voltage Gain	Av		100 300			100 300		V/mV V/mV	$R_L = 100$ KΩ $R_L = 1$ MΩ
Output Voltage Range	VO low	4.99	0.001 4.999	0.01	4.99	0.001 4.999	0.01	V V	R <sub>L</sub> = 1M $\Omega$ , V <sup>+</sup> = +5V 0°C ≤ T <sub>A</sub> ≤ +70°C
	VO low	2.40	-2.48 2.48	-2.40	2.40	-2.48 2.48	-2.40	V V	R <sub>L</sub> =100KΩ 0°C ≤ T <sub>A</sub> ≤ +70°C
Output Short Circuit Current	ISC		1			1		mA	
Supply Current	IS		240	360		240	360	μΑ	V <sub>IN</sub> = 0V, No Load
Power Dissipation	PD			1.8			1.8	mW	VS = ±2.5V
Input Capacitance	C <sub>IN</sub>		1			1		pF	
Bandwidth	BW		700			700		KHz	
Slew Rate	SR		0.7			0.7		V/μs	Aγ= +1, R <sub>L</sub> =100KΩ

### OPERATING ELECTRICAL CHARACTERISTICS (cont'd)

 $T_A = 25^{\circ}C$   $V_S = \pm 2.5V$  unless otherwise specified (cont'd)

		P	LD2731	١	1	ALD2731			
Parameter	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test Conditions
Rise time	t <sub>r</sub>		0.2			0.2		μS	R <sub>L</sub> = 100KΩ
Overshoot Factor			20			20		%	$R_L = 100K\Omega$ , $C_L = 50pF$
Settling Time	ts		10			10		μs	0.1%, A <sub>V</sub> = 100, R <sub>L</sub> = 100KΩ, C <sub>L</sub> = 50pF
Channel Separation	CS		140			140		dB	Ay = 100

 $T_A = 25^{\circ}C$   $V_S = \pm 5.0V$  unless otherwise specified

			ALD2731	A	ALD2731				
Parameter	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test Conditions
Power Supply Rejection Ratio	PSRR		90			90		dB	R <sub>S</sub> ≤ 100KΩ
Common Mode Rejection Ratio	CMRR		90			90		dB	R <sub>S</sub> ≤ 100KΩ
Large Signal Voltage Gain	Av		250			250		V/mV	R <sub>L</sub> = 100KΩ
Output Voltage Range	V <sub>O</sub> low V <sub>O</sub> high	4.90	-4.98 4.98	-4.90	4.90	-4.98 4.98	-4.90	V	R <sub>L</sub> = 100KΩ
Bandwidth	B <sub>W</sub>		1.0			1.0		MHz	
Slew Rate	S <sub>R</sub>		1.0			1.0		V/μs	A <sub>V</sub> = +1, C <sub>L</sub> = 50pF

 $V_S$  =  $\pm 2.5 V$  -55°C  $\leq T_A \leq +125^{\circ} C$  unless otherwise specified

		ALD2731A		ALD2731					
Parameter	Symbol	Min	Тур	Max	Min	Тур	Max	Unit	Test Conditions
Input Offset Voltage	Vos			2.0			3.0	mV	R <sub>S</sub> ≤ 100KΩ
Input Offset Current	los			2.0			2.0	nA	
Input Bias Current	ΙΒ			2.0			2.0	nA	
Power Supply Rejection Ratio	PSRR		75			75		dB	RS ≤ 100KΩ
Common Mode Rejection Ratio	CMRR		83			83		dB	RS ≤ 100KΩ
Large Signal Voltage Gain	Ay		50			50		V/mV	R <sub>L</sub> = 100KΩ
Output Voltage Range	VO low	2.35	-2.47 2.45	-2.40	2.35	-2.47 2.45	-2.40	V V	R <sub>L</sub> = 100KΩ

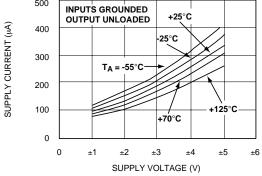
### **Design & Operating Notes:**

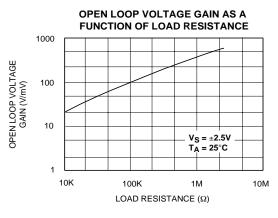
- 1. The ALD2731A/ALD2731 CMOS operational amplifier uses a 3 gain stage architecture and an improved frequency compensation scheme to achieve large voltage gain, high output driving capability, and better frequency stability. In a conventional CMOS operational amplifier design, compensation is achieved with a pole splitting capacitor together with a nulling resistor. This method is, however, very bias dependent and thus cannot accommodate the large range of supply voltage operation as is required from a stand alone CMOS operational amplifier. The ALD2731A/ALD2731 is internally compensated for unity gain stability using a novel scheme that does not use a nulling resistor. This scheme produces a clean single pole roll off in the gain characteristics while providing for more than 70 degrees of phase margin at the unity gain frequency.
- The ALD2731A/ALD2731 has complementary p-channel and nchannel input differential stages connected in parallel to accomplish rail to rail common mode input voltage ranges. This means that with the ranges of common mode input voltage close to the power supplies, one of the two differential stages is switched off internally. To maintain compatibility with other operational amplifiers, this switching point has been selected to be about 1.5V below the positive supply voltage. Since offset voltage trimming on the ALD2731A/ ALD2731 is made when the input voltage is symmetrical to the supply voltages, this internal switching does not affect a large variety of applications such as an inverting amplifier or non-inverting amplifier with a gain larger than 2.5 (5V operation), where the common mode voltage does not make excursions below this switching point. The user should, however, be aware that this switching does take place if the operational amplifier is connected as a unity gain buffer and should make provisions in the design to allow for input offset voltage variations.
- The input bias and offset currents are essentially input protection diode reverse bias leakage currents, and are typically 0.01pA at room temperature. This low input bias current assures that the analog signal from the source will not be distorted by input bias currents.

- Normally, this extremely high input impedance of greater than  $10^{14} \Omega$ would not be a problem as the source impedance would limit the node impedance. However, for applications where source impedance is very high, it may be necessary to limit noise and hum pickup through proper shielding.
- 4. The output stage consists of class AB complementary output drivers, capable of driving a low resistance load. The output voltage swing is limited by the drain to source on-resistance of the output transistors as determined by the bias circuitry, and the value of the load resistor. When connected in the voltage follower configuration, the oscillation resistant feature, combined with the rail to rail input and output feature, makes an effective analog signal buffer for medium to high source impedance sensors, transducers, and other circuit networks.
- 5. The ALD2731A/ALD2731 operational amplifier has been designed to provide full static discharge protection. Internally, the design has been carefully implemented to minimize latch up. However, care must be exercised when handling the device to avoid strong static fields that may degrade a diode junction, causing increased input leakage currents. In using the operational amplifier, the user is advised to power up the circuit before, or simultaneously with, any input voltages applied and to limit input voltages not to exceed 0.3V of the power supply voltage levels.
- 6. The ALD2731A/ALD2731, with its micropower operation, offers numerous benefits in reduced power supply requirements, less noise coupling and current spikes, less thermally induced drift, better overall reliability due to lower self heating, and lower input bias current. It requires practically no warm up time as the chip junction heats up to only 0.1°C above ambient temperature under most operating conditions.
- 7. The ALD2731A/ALD2731 has an internal design architecture that provides robust high temperature operation. Contact factory for custom screening versions.

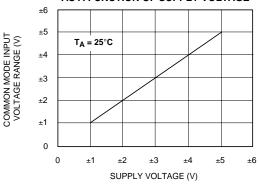
### TYPICAL PERFORMANCE CHARACTERISTICS

#### SUPPLY CURRENT AS A FUNCTION OF SUPPLY VOLTAGE 500 INPUTS GROUNDED +25°C **OUTPUT UNLOADED** 400

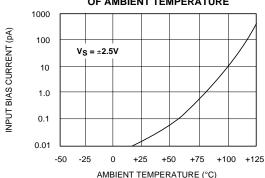




### **COMMON MODE INPUT VOLTAGE RANGE** AS A FUNCTION OF SUPPLY VOLTAGE

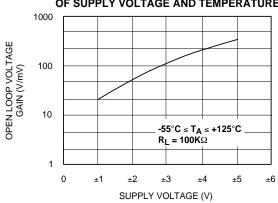


### INPUT BIAS CURRENT AS A FUNCTION OF AMBIENT TEMPERATURE

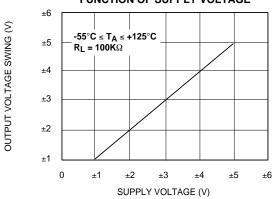


### TYPICAL PERFORMANCE CHARACTERISTICS (cont'd)

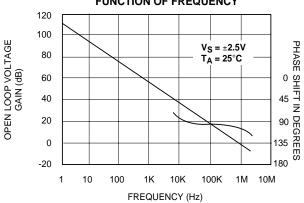
OPEN LOOP VOLTAGE GAIN AS A FUNCTION OF SUPPLY VOLTAGE AND TEMPERATURE



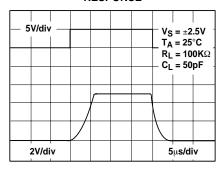
OUTPUT VOLTAGE SWING AS A FUNCTION OF SUPPLY VOLTAGE



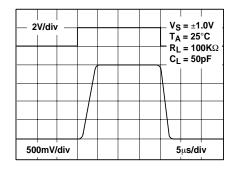
OPEN LOOP VOLTAGE GAIN AS A FUNCTION OF FREQUENCY



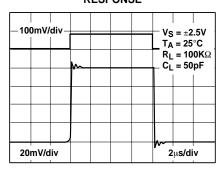
LARGE-SIGNAL TRANSIENT RESPONSE



LARGE-SIGNAL TRANSIENT RESPONSE



SMALL-SIGNAL TRANSIENT RESPONSE

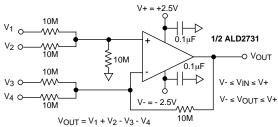


### TYPICAL APPLICATIONS

### RAIL-TO-RAIL VOLTAGE FOLLOWER/BUFFER

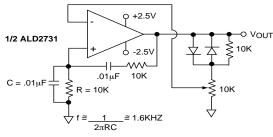
# $Z_{IN} \cong 10^{12} \Omega$ $V_{IN} \circ OUTPUT$ $U = V_{IN} \leq 5V$ \* See Rail to Rail Waveform

### HIGH INPUT IMPEDANCE RAIL-TO-RAIL PRECISION DC SUMMING AMPLIFIER



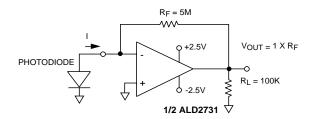
 $R_{IN}$  = 10M $\Omega$  Accuracy limited by resistor tolerances and input offset voltage

### WIEN BRIDGE OSCILLATOR (RAIL-TO-RAIL) SINE WAVE GENERATOR

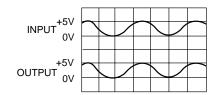


<sup>\*</sup> See Rail to Rail Waveform

## PHOTO DETECTOR CURRENT TO VOLTAGE CONVERTER

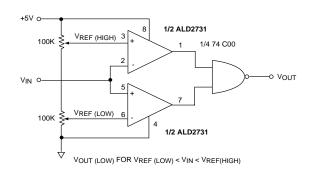


### **RAIL-TO-RAIL WAVEFORM**

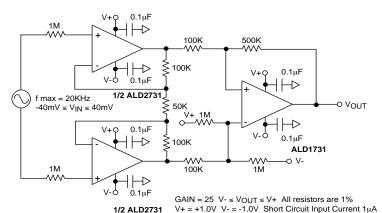


# Performance waveforms. Upper trace is the output of a Wien Bridge Oscillator. Lower trace is the output of Rail-to-rail voltage follower.

### **RAIL-TO-RAIL WINDOW COMPARATOR**

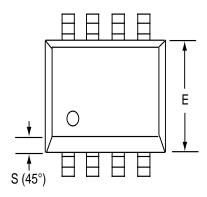


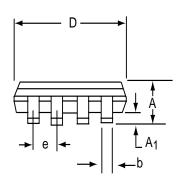
### LOW VOLTAGE INSTRUMENTATION AMPLIFIER



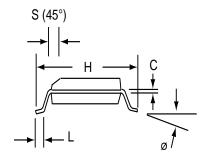
### **SOIC-8 PACKAGE DRAWING**

### 8 Pin Plastic SOIC Package



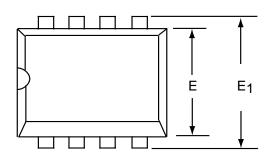


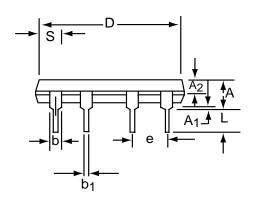
	Millim	neters	Inc	hes
Dim	Min	Max	Min	Max
Α	1.35	1.75	0.053	0.069
A <sub>1</sub>	0.10	0.25	0.004	0.010
b	0.35	0.45	0.014	0.018
С	0.18	0.25	0.007	0.010
D-8	4.69	5.00	0.185	0.196
E	3.50	4.05	0.140	0.160
е	1.27	BSC	0.050	BSC
Н	5.70	6.30	0.224	0.248
L	0.60	0.937	0.024	0.037
Ø	0°	8°	0°	8°
S	0.25	0.50	0.010	0.020



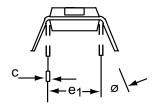
### **PDIP-8 PACKAGE DRAWING**

### 8 Pin Plastic DIP Package



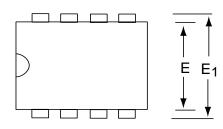


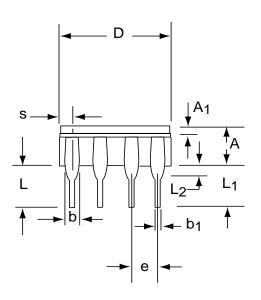
	Millim	neters	Inches				
Dim	Min	Max	Min	Max			
Α	3.81	5.08	0.105	0.200			
A <sub>1</sub>	0.38	1.27	0.015	0.050			
A <sub>2</sub>	1.27	2.03	0.050	0.080			
b	0.89	1.65	0.035	0.065			
b <sub>1</sub>	0.38	0.51	0.015	0.020			
С	0.20	0.30	0.008	0.012			
D-8	9.40	11.68	0.370	0.460			
E	5.59	7.11	0.220	0.280			
E <sub>1</sub>	7.62	8.26	0.300	0.325			
е	2.29	2.79	0.090	0.110			
e <sub>1</sub>	7.37	7.87	0.290	0.310			
L	2.79	3.81	0.110	0.150			
S-8	1.02	2.03	0.040	0.080			
Ø	0°	15°	0°	15°			

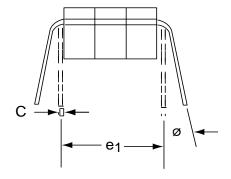


### **CERDIP-8 PACKAGE DRAWING**

### 8 Pin CERDIP Package







	Millin	neters	Inc	hes		
Dim	Min	Max	Min	Max		
Α	3.55	5.08	0.140	0.200		
A <sub>1</sub>	1.27	2.16	0.050	0.085		
b	0.97	1.65	0.038	0.065		
b <sub>1</sub>	0.36	0.58	0.014	0.023		
С	0.20	0.38	0.008	0.015		
D-8		10.29		0.405		
E	5.59	7.87	0.220	0.310		
E <sub>1</sub>	7.73	8.26	0.290	0.325		
е	2.54 E	BSC	0.100 BSC			
e <sub>1</sub>	7.62 E	BSC	0.300	BSC		
L	3.81	5.08	0.150	0.200		
L <sub>1</sub>	3.18		0.125			
L <sub>2</sub>	0.38	1.78	0.015	0.070		
S		2.49		0.098		
Ø	0°	15°	0°	15°		